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### Complete if Known

Application Number	10/046,346
Filing Date	October 26, 2001
First Named Inventor	Joseph J. Sumakeris et al.
Group Art Unit	2832-2811
Examiner Name	G. Munson

Attorney Docket Number

5000.221

### OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
29/39	1	PHILIP G. NEUDECK ET AL., 2000 V 6H-SiC p-n junction diodes grown by chemical vapor deposition, Applied Physics Letters, March 14, 1994, pages 1386-1388, Volume 64, No. 11, American Institute of Physics, New York, US	
	2	SEI-HYUNG RYU ET AL., 1800 V NPN Bipolar Junction Transistors in 4H-SiC, IEEE Electron Device Letters, March 2001, pages 124-126, Volume 22, No. 3, IEEE Inc., New York, US	
	3	SEI-HYUNG RYU ET AL., 3100 V, Asymmetrical, Gate Turn-Off (GTO) Thyristors in 4H-SiC, IEEE Electron Device Letters, March 2001, pages 127-129, Volume 22, No. 3, IEEE Inc, New York, US	
	4	J.W. PALMOUR ET AL., Silicon Carbide for Power Devices, Power Semiconductor Devices and IC's, IEEE International Symposium on Weimar, Germany, May 26-29, 1997, pages 25-32, IEEE, New York, US	
29/39	5	J.P. BERGMAN ET AL., Defects in 4H silicon carbide, 21 <sup>st</sup> International Conference on Defects in Semiconductors, Giessen, Germany, July 16-20, 2001, Physica B, December 2001, pages 675-679, Volume 308-310, Elsevier, Netherlands	
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